

DESCRIPTION

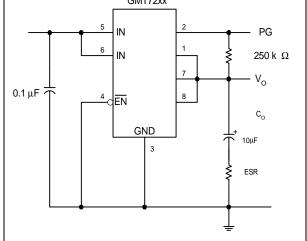
The GMT72xx Family of Micropower, low dropout (LDO) voltage regulators offer efficient, low-dropout performance as required by modern portable applications such as palmtop computers, two-way paging, portable telephones, and global positioning equipment (GPS). Compared to conventional LDO IC's, these regulators perform at low quiescent operating current with significantly lower dropout voltages. Available in 8-pin SOIC and DIP packages, these devices provide reliable, low cost solutions for contemporary mobile system needs. The GMT7201 provides additional flexibility by allowing a user to set the output voltage with the use of an external resistor feedback-divider. System power management control is permitted with the use of an enable pin.

Enhanced LDO performance is provided by the use of an advanced PMOS pass transistor design and is a significant improvement over conventional bipolar technology. Similarly, parasitic substrate or ground currents are virtually eliminated by the improved design. The PMOS pass element behaves as a low-value resistor, the drop-out voltage is very low with a maximum of 85 mV at 100 mA of load current. The improved CMOS architecture significantly reduces the operating current which aids in extending the life expectancy of on-board, replaceable or rechargeable power sources.

FEATURES

- Available in 5.0 Volt, 4.85 Volt, and 3.3 Volt Fixed Output and Adjustable Product Options.
- When $I_0 = 100$ mA, Maximum Dropout Voltage is < 85 mVolts (GMT7250).
- Typical Quiescent Current is 180 µA, Independent of Load.
- 8 Pin Plastic DIP and SOIC Package Options Available.
- Fixed Output Versions* Output Regulated to +/- 2% Over Entire Operating Range.
- Logic Enabled Sleep Mode Results in Sleep-State Current of 0.5 uA.

TYPICAL APPLICATION CONFIGURATION GMT72xx

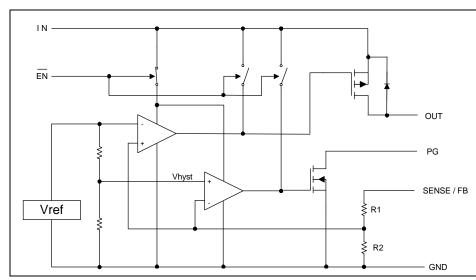


*Fixed voltage options: GMT7233, GMT7248 and GMT7250

Table 1: GMT72xx FAMILY

PART NO.	DESCRIPTION
7201	ADJUSTABLE REGULATOR
7233	3.3 V REGULATOR
7248	4.85 V REGULATOR
7250	5.0 V REGULATOR

FUNCTIONAL BLOCK DIAGRAM



 $\begin{array}{c|cccc} \textbf{RESISTOR DIVIDER OPTIONS} \\ \hline \textbf{DEVICE} & \textbf{R1} & \textbf{R2} & \textbf{Unit} \\ \hline \textbf{GMT7201} & \textbf{0} & \infty & \Omega \\ \hline \textbf{GMT7233} & \textbf{420} & \textbf{233} & \textbf{K}\Omega \\ \hline \textbf{GMT7248} & \textbf{726} & \textbf{233} & \textbf{K}\Omega \\ \hline \textbf{GMT7250} & \textbf{756} & \textbf{233} & \textbf{K}\Omega \\ \hline \end{array}$

Resistor values are nominal

Note: Out and Sense must be tied together as close as possible to the device.

Table 2: ABSOLUTE MAXIMUM RATINGS OVER OPERATING TEMPERATURE RANGE (FREE AIR UNLESS OTHERWISE NOTED)¹

Input Voltage Range ² , V _I , PG, SENSE, EN0.3 V to 11	٧
Output Current, I _O	5 A
Continuous Total Power Dissipation See Dissipation Rating Tables 1 and	d 2
Operating Virtual Junction Temperature Range, T _J 55°C to 150°	'C
Storage Temperature Range T _{stg} 65°C to 150°	,C
Lead Temperature, 1, 6 mm, (1/16 inch) from case for 10 sec	οС

¹ Stresses beyond those listed in this table may cause permanent damage to the device. These are stress ratings only and functional operation of the device, at these or any other conditions beyond those indicated under Recommended Operating Conditions (Table 2), is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

² All voltage values are with respect to network ground terminal.

PACKAGE TYPES

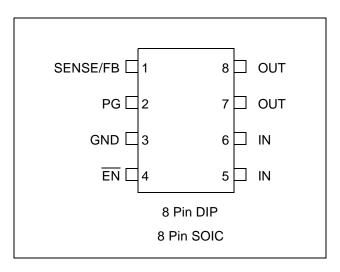


Table 3: AVAILABLE OPTIONS

TJ	OUTPUT VOLTAGE			PACKAGE TYPES		
1,1	MIN	TYPICAL	MAX	SOIC	DIP	
	4.9	5.0	5.1	GMT7250M	GMT7250N	
-55°C to 150°C	4.75	4.85	4.95	GMT7248M	GMT7248N	
150°C —	3.23	3.3	3.37	GMT7233M	GMT7233N	
	Adjus	table: 1.2 V to 9	.75 V	GMT7201M	GMT7201N	

The ANM package is available in tape and reel; add T to the part number.

Table 4: USAGE DESCRIPTIONS

PIN	NAME	USAGE DESCRIPTION
1	SENSE/FB	Normally tied to Vout except for adjustable version. Refer to the Applications section.
2	PG	Power Good indicator; normally tied to Vout with a 250 K resistor. Pulls low when Vout drops below 0.95 of regulated output voltage.
3	GND	Reference point and return of circuit.
4	EN	Allows control of the LDO with TTL compatible signal. LOW = REG ON
5,6	Vin	Input voltage and filter capacitor are applied here.

Table 4: USAGE DESCRIPTIONS

PIN	NAME	USAGE DESCRIPTION
7,8		Vout output voltage appears here. Filter capacitor is also applied here.

Table 5: RECOMMENDED OPERATING CONDITIONS

		MIN	MAX	UNITS
Input Voltage, V _I [†]	GMT7201	3.0	10	V
	GMT7233	3.98	10	V
input voltage, v ₁	GMT7248	5.24	10	V
	GMT7250	5.41	10	V
High-level input voltage at EN, V _{IH}		2.0		V
Low-level input voltage at EN, V _{IL}			0.5	V
Output Current, I _O		0.0	250	mA
Operating virtual junction Temperature, T _J		-40	125	°C

[†]Minimum input voltage defined in the recommended operating conditions is the maximum specified output voltage plus dropout voltage at the maximum specified load range. Since dropout voltage is a function of output current, the usable range can be extended for lighter loads. To calculate the minumum input voltage for the maximum load current used in a given application, use the following equation:

$$V_{I(min)} = V_{O(max)} + V_{DO(max load)}$$

Because the GMT7201 is programmable, $r_{DS(on)}$ should be used to calculate V_{DO} before applying the above equation. The equation for calculating V_{DO} from $r_{DS(on)}$ is given in Note 2, Page 6 under GMT7201 electrical characteristics table. The minimum value of 3.0 V is the absolute lower limit for the recommended input-voltage range for the GMT7201.

Table 6: ELECTRICAL CHARACTERISTICS (PACKAGED DEVICES) $I_O = 10$ mA, EN = 0 V, $C_O = 4.7$ μF(CSR = 1 Ω), $T_J = 25$ °C, SENSE/FB shorted to OUT (unless otherwise noted). CSR refers to the total of capacitor ESR lead resistance and PWB trace resistance.

PARAMETER	TEST CONDITIONS [†]	TJ	GM ¹ GM	UNITS			
	1201 GONDING		MIN	TYP	MAX		
Ground Current (active mode)	$\overline{\text{EN}} \le 0.5 \text{ V}, \text{ V}_{\text{I}} = \text{V}_{\text{O}} + 1.0 \text{ V}, 0.0$ $\text{mA} \le \text{I}_{\text{O}} \le 250 \text{ mA}$	25°C		180	225	μА	
modely	111A <u>C10C</u> 230 111A	-40°C to 125°C			325	μ	
Input Current (standby mode)	EN = V _I , 2.7 V≤V _I ≤10 V	25°C			0.5	μΑ	
	214 - 41, 2.1 4241210 4	-40°C to 125°C			1.0	μ	
Output Current Limit Threshold	V _O = 0.0 V, V _I = 10 V	25°C		0.6	1.0	А	
		-40°C to 125°C			1.5	,,	
Pass-element Leakage Current in Standby Mode	EN = V _I , 3.0 V≤V _I ≤10 V.	25°C			0.5	μА	
		-40°C to 125°C			1.0	μΛ	
PG Leakage Current	V _{PG} = 10 V Normal Operation	25°C			0.5	μА	
	rtomai oporation	-40°C to 125°C			0.5	,	
Output Voltage Temperature Coefficient		-40°C to 125°C		31	75	ppm/°C	
Thermal Shutdown Junction Temperature				150		°C	
EN Logic High (Standby Mode)	3.0 V ≤ V _I ≤ 6.0 V	-40°C to 125°C	2.0			V	
mode)	6.0 V ≤ V _I ≤ 10 V	-40 C to 125 C	2.7			v	
EN Logic Low (Active Mode)	3.0 V ≤ V _I ≤ 10 V	25°C			0.5	V	
,		-40°C to 125°C			0.5		
EN Hysteresis Voltage		25°C		50		mV	
EN Input Current	0.0 V ≤ V _I ≤ 10 V	25°C	-0.5		0.5	μА	
		-40°C to 125°C	-0.5		0.5	,	
Minimum V _I for active pass element		25°C		1.9	2.5	V	
pass diement		-40°C to 125°C			2.5	•	
Minimum V _I for valid PG	IPG = 300 μA	25°C		0.95	1.5	V	
	Ο σσο μι	-40°C to 125°C			1.9	•	

[†]Pulse-testing techniques are used to maintain Ta=Tj.

Table 7: ELECTRICAL CHARACTERISTICS (DIE FORM) I_O = 10 mA, $\overline{\text{EN}}$ = 0 V, C_O = 4.7 $\mu\text{F}(\text{CSR}$ = 1 $\Omega)$, T_J = 25°C, SENSE/FB shorted to OUT (unless otherwise noted). CSR refers to the total of capacitor ESR lead resistance and PWB trace resistance.

PARAMETER	TEST CONDITIONS†	GMT7201,GMT7233, GMT7248,GMT7250			UNITS
		MIN	TYP	MAX	
Ground Current (Active Mode)	$\overline{\rm EN} \le 0.5 \rm V, V_I = V_O + 1.0 \rm V,$ $0.0 \rm mA \le I_O \le 250 \rm mA$		180		μΑ
Output Current Limit Threshold	V _O = 0.0 V, V _I = 10 V		0.6		Α
Thermal Shutdown Junction Temperature			165		°C
EN Hysteresis Voltage			50		mV
Minimum V _I for active pass element			1.9		V
Minimum V _I for valid PG	I _{PG} - 300 μA		0.95		V

[†]Pulse-testing techniques are used to maintain Ta=Tj.

Table 8: ELECTRICAL CHARACTERISTICS (GMT7201) I_O = 10 mA, \overline{EN} = 0 V, C_O = 4.7 μ F(CSR = 1 Ω), T_J = 25°C, SENSE/FB shorted to OUT (unless otherwise noted). CSR refers to the total of capacitor ESR lead resistance and PWB trace resistance.

DADAMETED			GMT7201				
PARAMETER	TEST CONDITIONS [†]	T _J	MIN	TYP	MAX	UNITS	
Reference voltage (mea-	V _I = 3.5 V, I _O = 10 mA	25°C		1.168		V	
sured at FB with OUT con- nected to FB)	$2.5 \text{ V} \le \text{V}_{\text{I}} \le 10 \text{ V}, 5.0 \text{ mA} \le \text{I}_{\text{O}} \le 250 \text{ mA}$ See Note 1	-40°C to 125°C	1.152		1.224	V	
Reference voltage tempera- ture coefficient		-40°C to 125°C		31	75	ppm/°C	
	$V_{I} = 2.4 \text{ V}, 50 \mu\text{A} \le I_{O} \le 100 \text{mA}$	25°C		2.1	4.2		
	ν - 2.4 ν, 30 μΛ <u>Σ</u> 1 <u>0</u> <u>Σ</u> 100 πΛ	-40°C to 125°C			4.8		
	$V_{I} = 2.4 \text{ V}, 100 \mu\text{A} \le I_{O} \le 200 \text{mA}$	25°C		2.9	4.4		
Pass-element series resis-	V - 2.4 V, 100 μΛ ≤ 10 ≤ 200 πΛ	$-40^{\circ}\text{C to } 125^{\circ}\text{C} \qquad \qquad 4.6$ $25^{\circ}\text{C} \qquad \qquad 1.6 \qquad 2.7$ $-40^{\circ}\text{C to } 125^{\circ}\text{C} \qquad \qquad 4.5$					
tance (see Note 2)	$V_{\parallel} = 2.9 \text{ V}, 50 \mu\text{A} \le I_{\bigcirc} \le 250 \text{mA}$	25°C		1.6	2.7	Ω	
		-40°C to 125°C			4.5		
	$V_{I} = 3.9 \text{ V}, 50 \mu\text{A} \le I_{O} \le 250 \text{ mA}$	25°C		1.0			
V _I =	$V_{I} = 5.9 \text{ V}, 50 \mu\text{A} \le I_{O} \le 250 \text{ mA}$	25°C		0.8			
Input regulation	$V_{I} = 2.5 \text{ V}, 50 \mu\text{A} \le I_{O} \le 250 \text{mA}$	25°C			23	mV	
input regulation	See Note 1	-40°C to 125°C			1.224 75 4.2 4.8 4.4 4.6 2.7 4.5	1111	
	$I_{O} = 5.0 \text{ mA to } 250 \text{ mA}, 2.5 \text{ V} \le \text{V}_{I} \le 10 \text{ V}$	25°C		15	25		
Output as sullations	See Note 1	-40°C to 125°C			36		
Output regulation	$I_{O} = 50 \mu\text{A} \text{ to } 250 \text{mA}, 2.5 \text{V} \leq \text{V}_{I} \leq 10 \text{V}$	25°C		17	27	- mV	
	See Note 1	-40°C to 125°C			4.6 1.6 2.7 4.5 1.0 0.8 23 36 15 25 36 17 27 43		
	ΙΟ = 50 μΑ	25°C	49	60			
Disals seisettes	.0 = 30 μΛ	-40°C to 125°C	32			-10	
Ripple rejection	I _O = 250 mA,	25°C	45	50		dB	
	See Note 1	-40°C to 125°C	30				
Output noise spectral density	1.0 = 120 Hz	25°C		2.0		μV/√ Hz	

[†]Pulse-testing techniques are used to maintain Ta=Tj.

¹ When V_I <2.9 V and I_O >100 mA simultaneously, pass element $r_{DS(on)}$ increases to a point such that the resulting dropout voltage prevents the regulator from maintaining the specified tolerance range.

² To calculate dropout voltage, use equation: $V_{DO} = I_O \ r_{DS(on)}$. $r_{DS(on)}$ is a function of both output current and input voltage. The parametric table lists $r_{DS(on)}$ for $V_I = 2.4 \ V$, 2.9 V, 3.9 V and 5.9 V, which corresponds to dropout conditions for programmed output voltages of 2.5 V, 3.0 V, 4.0 V and 6.0 V, respectively.

Table 8: ELECTRICAL CHARACTERISTICS (GMT7201) Cont.

PARAMETER	TEST CONDITIONS [†]	TJ	GMT7201			UNITS
FARAMETER	TEST CONDITIONS	·J	MIN	TYP	0.4 0.4 10 20	UNITS
	C _O = 4.7 μF	25°C		235		
Ouput noise voltage	C _O = 10 μF	25°C		190		μVrms
	C _O = 100 μF	25°C		195		
PG trip-threshold voltage	V _{FB} voltage decreasing from above V _{PG}	-40°C to 125°C		0.95 x V _{FB(nom)}		V
PG hysteresis voltage	Measured at V _{FB}	25°C		12		mV
PG output low voltage	I _{PG} = 400 μA, V _I = 2.13 V	25°C		0.1	0.4	V
PG output low voltage		-40°C to 125°C			0.4	V
ED input ourrent		25°C	-10	0.1	10	nA
FB input current		-40°C to 125°C	-20		20	ПА

[†]Pulse-testing techniques are used to maintain Ta=Tj.

Table 9: ELECTRICAL CHARACTERISTICS (GMT7233)

 I_O = 10 mA, \overline{EN} = 0 V, C_O = 4.7 μF (CSR = 1 Ω), T_J = 25°C, SENSE/FB shorted to OUT (unless otherwise noted. CSR refers to the total of capacitor ESR lead resistance and PWB trace resistance.

PARAMETER	t	T _J	GMT7233			UNITS
PARAMETER	TEST CONDITIONS [†]	' J	MIN	TYP	3.37 20 30 180 232 460 610 1.84 2.5 25 33	UNITS
Outsutualtana	V _I = 4.3 V, I _O = 10 mA	25°C		3.3		V
Output voltage	$4.3 \text{ V} \le \text{V}_{1} \le 10 \text{ V}, 5.0 \text{ mA} \le \text{I}_{O} \le 250 \text{ mA}$	-40°C to 125°C	3.23		3.37	V
	I _O = 10 mA, V _I = 3.23 V	25°C		14	20	
	10 = 10 mA, V[= 3.25 V	-40°C to 125°C			30	mV
5	I _O = 100 mA, V _I = 3.23 V	25°C		140	180	
Dropout voltage		-40°C to 125°C			232	
	I _O = 250 mA, V _I = 3.23 V	25°C		360	460	
		-40°C to 125°C			610	
Pass-element series	(3.23 V - V _O)/I _O ,V _I = 3.23 V, I _O = 250	25°C		1.5	1.84	0
resistance	mA	-40°C to 125°C			2.5	Ω
Input regulation	$V_1 = 4.3 \text{ V to } 10 \text{ V}, 50 \mu\text{A} \leq I_{\bigcirc} \leq 250 \text{ mA}$	25°C		8.0	25	mV
input regulation	- 1 τ το τ, σο μπ. Σ 10 Σ 200 ππ.	-40°C to 125°C			33	IIIV

[†]Pulse-testing techniques are used to maintain Ta=Tj.

Table 9: ELECTRICAL CHARACTERISTICS (GMT7233) Cont.

PARAMETER		т.		GMT7233		LINUTO
PARAMETER	TEST CONDITIONS [†]	T_J	MIN	TYP	MAX	UNITS
	$I_{O} = 5.0 \text{ mA to } 250 \text{ mA}, 4.3 \text{ V} \le \text{V}_{I} \le 10 \text{ V}$	25°C		32	42	
Outside as sulption	10 = 3.0 mix to 200 mix, 4.3 V <u>< V 5</u> 10 V	-40°C to 125°C			71	\/
Output regulation	$I_{O} = 50 \mu A \text{ to } 250 \text{ mA}, 4.3 \text{ V} \le \text{V}_{I} \le 10 \text{ V}$	25°C		41	55	mV
	10 = 30 μλ to 200 mλ, 4.3 ν <u>ς ν</u> ς 10 ν	-40°C to 125°C			98	
	I _O = 50 μA	25°C	40	52		
Dipple rejection	ΙΟ = 50 μΑ	-40°C to 125°C	38			40
Ripple rejection	I _O = 250 mA	25°C	35	44		dB -
		-40°C to 125°C	33			
Output noise spectral density	f = 120 Hz	25°C		2.0		μV/√ Hz
	C _O = 4.7 μF	25°C		265		
Output noise voltage	$C_{O} = 10 \mu F$	25°C		212		μVrms
	$C_{O} = 100 \mu\text{F}$	25°C		135		
PG trip-threshold voltage	V _O voltage decreasing from above V _{PG}	-40°C to 125°C		0.95 x V _{O(nom)}		V
PG hysteresis voltage		25°C		32		mV
PG output low voltage	1.0pg = 1.2 mA, V _I = 2.8 V	25°C		0.22	0.4	V
1 O output low voltage		-40°C to 125°C			0.4	v

[†]Pulse-testing techniques are used to maintain Ta=Tj.

Table 10: PACKAGE THERMAL COEFFICIENTS

8 PIN DIP	8.5mW/ deg.C
8 PIN SOIC	5.8mW/ deg.C

Table 11: ELECTRICAL CHARACTERISTICS (GMT7248)

 I_O = 10 mA, \overline{EN} = 0 V, C_O = 4.7 μF (CSR = 1 Ω), T_J = 25°C, SENSE/FB shorted to OUT (unless otherwise noted. CSR refers to the total of capacitor ESR lead resistance and PWB trace resistance.

PARAMETER		т	GMT7248			
	TEST CONDITIONS [†]	T _J	MIN	TYP	MAX	UNITS
	V _I = 5.85 V, I _O = 10 mA	25°C		4.85		
Output voltage	5.85 V ≤ V _I ≤ 10 V, 5.0 mA≤ I _O ≤ 250 mA	-40°C to 125°C	4.75		4.95	V
	I _O = 10 mA, V _I = 4.75 V	25°C		10	19	
	10 = 10 1111, 17 = 1.70 1	-40°C to 125°C			30	
Dropout voltage	I _O = 100 mA, V _I = 4.75 V	25°C		90	100	m\/
Dropout voltage	10 = 100 1111 (, V) = 11.70 V	-40°C to 125°C			150	- mV
	I _O = 250 mA, V _I = 4.75 V	25°C		216	250	
	10 = 200 111/1, V = 4.70 V	-40°C to 125°C			285	1
Pass-element series	$(4.75 \text{ V} - \text{V}_{\mbox{O}})/I_{\mbox{O}}, \mbox{V}_{\mbox{I}} = 4.75 \text{ V}, \mbox{I}_{\mbox{O}} = 250$ mA	25°C		0.8	1.0	
resistance		-40°C to 125°C			1.4	Ω
land an addition	$V_{I} = 5.85 \text{ V to } 10 \text{ V}, 50 \mu\text{A} \le I_{O} \le 250 \text{ mA}$	25°C			34	mV
Input regulation		-40°C to 125°C			50	
	I_{\bigodot} = 5.0 mA to 250 mA, 5.85 V \leq V $_{\i}$ \leq 10 V	25°C		43	55	mV
Outrant or mulation		-40°C to 125°C			95	
Output regulation	$I_{O} = 50 \mu\text{A} \text{ to } 250 \text{mA}, 5.85 \text{V} \leq \text{V}_{\text{I}} \leq 10 \text{V}$	25°C		55	75	
		-40°C to 125°C			135	
	I _O = 50 μA	25°C	42	53		- dB
Disab sais stice		-40°C to 125°C	36			
Ripple rejection	I _O = 250 mA	25°C	36	46		
		-40°C to 125°C	34			
Output noise spectral density	f = 120 Hz	25°C		2.0		μV/√ Hz
Output noise voltage	C _O = 4.7 μF	25°C		370		
	C _O = 10 μF	25°C		290		μVrms
	C _O = 100 μF	25°C		168		1
PG trip-threshold voltage	V _O voltage decreasing from above V _{PG}	-40°C to 125°C		0.95 x V _{O(nom)}		V

[†]Pulse-testing techniques are used to maintain Ta=Tj.

PRELIMINARY GMT72xx FAMILY LOW DROP-OUT VOLTAGE REGULATORS

Table 10: ELECTRICAL CHARACTERISTICS (GMT7248) Cont.

PARAMETER	TEGT CONDITIONS [†]	T _J	GMT7248			UNITS
	TEST CONDITIONS [†]		MIN	TYP	MAX	ONIIS
PG hysteresis voltage		25°C		50		mV
PG output low voltage $1p_G = 1.2 \text{ mA}, V_I = 4.12 \text{ V}$	1pc = 1 2 mA Vi = 4 12 V	25°C		0.2	0.4	\/
	196-12111, 11-4.12	-40°C to 125°C			0.4	٧

[†]Pulse-testing techniques are used to maintain Ta=Tj.

Table 12: ELECTRICAL CHARACTERISTICS (GMT7250)

 I_O = 10 mA, \overline{EN} = 0 V, C_O = 4.7 μF (CSR = 1 Ω), T_J = 25°C, SENSE/FB shorted to OUT (unless otherwise noted. CSR refers to the total of capacitor ESR lead resistance and PWB trace resistance.

DADAMETED	+	TJ	GMT7250			UNITS
PARAMETER	TEST CONDITIONS [†]	. 1	MIN	TYP	MAX	ONITS
	V _I = 6.0 V, I _O = 10 mA	25°C		5.0		
Output voltage	$6.0 \text{ V} \le \text{V}_{\text{I}} \le 10 \text{ V}, 5.0 \text{ mA} \le \text{I}_{\text{O}} \le 250 \text{ mA}$	-40°C to 125°C	4.9		5.1	V
	IO = 10 mA, VI = 4.88 V	25°C		8.0	12	
	10 = 10 111/1, V = 4.00 V	-40°C to 125°C			30	
Dropout voltage	I _O = 100 mA, V _I = 4.88 V	25°C		76	85	mV
Dropout voltage	10 = 100 111/1, 17 = 1.00 1	-40°C to 125°C			136	IIIV
	IO = 250 mA, VI = 4.88 V	25°C		190	206	
	10 = 250 m/s, v = 4.00 v	-40°C to 125°C		312		
Pass-element series	(4.88 V - V _O)/I _O ,V _I = 4.88 V, I _O = 250	25°C		0.78	0.825	
resistance	mA	-40°C to 125°C	1.25	Ω		
	$V_{I} = 6.0 \text{ V to } 10 \text{ V}, 50 \mu\text{A} \leq I_{O} \leq 250 \text{ mA}$	25°C			28	- mV
Input regulation		-40°C to 125°C			35	
	I _O = 5.0 mA to 250 mA, 6.0 V <u><</u> V _I ≤ 10 V	25°C		46	61	
Outside as suitables	10 = 3.0 IIIA to 230 IIIA, 0.0 V <u>~</u> V <u>~</u> 10 V	-40°C to 125°C			100	
Output regulation	$I_O = 50 \mu\text{A} \text{ to } 250 \text{mA}, 6.0 \text{V} \leq \text{V}_I \leq 10 \text{V}$	25°C		59	79	- mV
	10 = 30 μΑ 10 230 ΠΑ, 0.0 ν <u>ε</u> ν <u>ε</u> 10 ν	-40°C to 125°C			150	
2	I _O = 50 μA	25°C	41	52		
	10 = 50 μΑ	-40°C to 125°C	37			٦.
Ripple rejection		25°C	36	46		- dB
	I _O = 250 mA	-40°C to 125°C	32			

[†]Pulse-testing techniques are used to maintain Ta=Tj.

Table 9: ELECTRICAL CHARACTERISTICS (GMT7250) Cont.

PARAMETER	t	T _J	GMT7250			UNITS
FANAMETER	TEST CONDITIONS [†]		MIN	TYP	MAX	UNITS
Output noise spectral density	f = 120 Hz	25°C		2.0		μV/√ Hz
	C _O = 4.7 μF	25°C		390		
Output noise voltage	C _O = 10 μF	25°C		300		μVrms
	C _O = 100 μF	25°C		175		
PG trip-threshold voltage	V _O voltage decreasing from above V _{PG}	-40°C to 125°C		0.95 x V _{O(nom)}		V
PG hysteresis voltage		25°C		50		mV
PG output low voltage	1.0 pg = 1.2 mA, V _I = 4.25 V	25°C		0.19	0.4	V
PG output low voltage	FG, . - 1.20 V	-40°C to 125°C			0.4	٧

[†]Pulse-testing techniques are used to maintain Ta=Tj.

GENERAL DEVICE DESCRIPTION

The GMT72xx regulator family has been specifically designed to operate within noise-prone switched mode environments. Line and Load regulation have been substantially improved over competing devices, and the ability of the POWER GOOD (PG) flag to resist switching noise transients has been dramatically improved. A PMOS series pass element is used, which leads to lower Vdropout differentials, which, in turn, eases system design requirements and extends battery utilization time. Current consumption, both in terms of sleep and ground currents, is kept to uA levels, which means that portable applications will benefit from increased battery life. All of these factors make the GMT72xx family an excellent choice for switched-mode, battery-powered portable applications.

As with all CMOS inputs, at no time should the ENABLE pin be floated. It must be either grounded (enabled) or tied to Vcc (off) for all applications. Resistive pull-up is acceptable as well. A 250 K pull-up resistor must be included from PG to Vout when using the PG flag feature.

SELECTION OF INPUT AND OUTPUT CAPACITORS

Standard design practice dictates that a ceramic input capacitor of approximately 0.1 uF be placed very close to the regulator input. This value may be adjusted to improve transient and ripple performance as needed.

The output capacitor plays an important role in stabilizing the LDO control loop, and should be a minimum value of 4.7 uF. If low ESR capacitor varieties such as Tantalum are used, a series resistor of 0.5 ohm may need to be included.

If a lower value of output capacitor must be used, it may be necessary to include a series resistance of up to 1.0 ohm in order to ensure stability of the device. The recommended minimum value for the output capacitor is 4.7 uF. Note that the ESR required for device stability is bounded by both upper and lower limits. Please contact GMT for further information.

SELECTING THE ADJUSTABLE VERSION (7201 SERIES) DIVIDER RESISTORS

When using the adjustable version, the external divider network must be selected to obtain the desired Vout. The first constraint on the divider network is the current draw, which is nominally set at 8.0 uA:

One Resistor may now be selected, and the other solved for, knowing what Vout value is desired. The fundamental equation Vo = Vref x (1 + (R1/R2)) is used; therefore, $R1 = R2 x \{[Vo/Vref] - 1\}$. Please see the following tabulation:

Figure 1

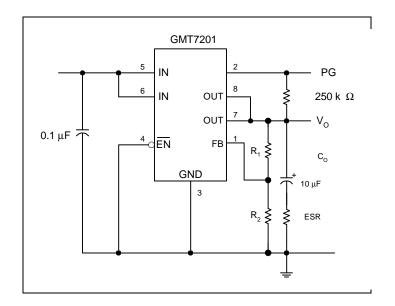


Table 13: GMT7201 ADJUSTABLE LDO DIVIDER VALUES

OUTPUT VOLTAGE	DIVIDER VALUES; 1% (KOHM)			
	R1	R2		
2.5	182 K	165 K		
3.0	249 K	165 K		
3.3	294 K	165 K		
3.6	332 K	165 K		
4.0	392 K	165 K		
4.5	464 K	165 K		
5.0	523 K	165 K		
6.4	732 K	165 K		

The Vout range of the 7201 series may be varied from approximately 1.2 V to 9.0 V. Resistor values may require adjustment to achieve desired set-points.

THERMAL CONSIDERATIONS

The GMT72xx has been designed with internal over-current limiting, set at approximately 600 mA, as well as junction temperature detection, which limits TJ to approximately 150°C. In the event of a current overload, Vo shuts down when TJ reaches 150°C. The LDO will then turn back on as the junction cools. Even though the device is well protected, the designer must still properly manage the thermal environment in order to maximize efficiency and reduce stress. Maximum power dissipation is given by **Pd (max) = (Tjmax-TA)/** R θ JA. Where Tjmax is maximum allowable junction temperature, TA is the ambient temperature

RθJA is the package thermal coefficient. These numbers are derived under specific, controlled test conditions. Actual thermal performance ultimately depends on the application. Each individual board design must be carefully evaluated over full temperature and operational extremes. Please refer to the package data section for thermal coefficients.

LIFE SUPPORT USAGE POLICY:

GMT's products are not authorized for use as critical components in life support devices or systems without the express written approval of the CEO of GMT. As used herein:

- (a) Life support devices or systems are devices or systems which (1) are intended for surgical implant into the body, or (2) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- (b) A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system.

GMT Microelectronics Corporation

Valley Forge Corporate Center 950 Rittenhouse Road Norristown, PA 19403

Toll Free: (888) GMT-4771 Ph: (610) 728-9300 Fax: (610) 676-7066

E-Mail: marketing @ gmtme.com Website: www.gmtme.com

Sales Offices